Features

- Low-voltage and Standard-voltage Operation
 - $-2.7 (V_{CC} = 2.7V \text{ to } 5.5V)$
 - 1.8 (V_{CC} = 1.8V to 5.5V)
- Three-wire Serial Interface
- 2 MHz Clock Rate (5V) Compatibility
- Self-timed Write Cycle (10 ms max)
 High Reliability
 - Endurance: 1 Million Write Cycles
 - Data Retention: 100 Years
- Automotive Grade, Extended Temperature, and Lead-free/Halogen-free Devices Available
- 8-lead PDIP, 8-lead JEDEC SOIC, and 8-lead TSSOP Packages

Description

The AT93C46A provides 1024 bits of serial electrically-erasable programmable readonly memory (EEPROM) organized as 64 words of 16 bits each. The device is optimized for use in many industrial and commercial applications where low-power and low-voltage operation are essential. The AT93C46A is available in space-saving 8lead PDIP, 8-lead JEDEC SOIC, and 8-lead TSSOP packages.

The AT93C46A is enabled through the Chip Select pin (CS) and accessed via a threewire serial interface consisting of Data Input (DI), Data Output (DO), and Shift Clock (SK). Upon receiving a Read instruction at DI, the address is decoded and the data is clocked out serially on the data output DO pin. The write cycle is completely self-timed and no separate erase cycle is required before write. The write cycle is only enabled when the part is in the erase/write enable state. When CS is brought high following the initiation of a write cycle, the DO pin outputs the ready/busy status of the part.

The AT93C46A is available in 2.7V to 5.5V and 1.8V to 5.5V versions.

Pin Name	Function		
CS	Chip Select		
SK	Serial Data Clock		
DI	Serial Data Input		
DO	Serial Data Output		
GND	Ground		
VCC	Power Supply		

Table 1. Pin Configuration

8-lead PDIP □ vcc CS T1 8 SK 🗆 2 7 D DC DI 🗌 3 6 $DO \square 4$ 5 🗌 GND 8-lead SOIC CS 🗆 8 1 SK [2 7 DI 🗆 3 6 DO 🗆 4 5 GND 8-lead TSSOP CS 8 SK [2 7 З 6 5 DO 4 🗆 GND



Three-wire Serial EEPROM

1K (64 x 16)

AT93C46A

Rev. 0539J-SEEPR-11/04

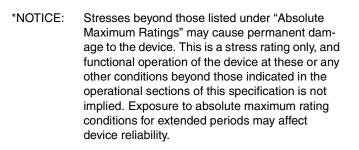




Absolute Maximum Ratings*

Operating Temperature55°C to +125°C
Storage Temperature65°C to +150°C
Voltage on Any Pin with Respect to Ground1.0V to +7.0V
Maximum Operating Voltage 6.25V
DC Output Current 5.0 mA

Figure 1. Block Diagram



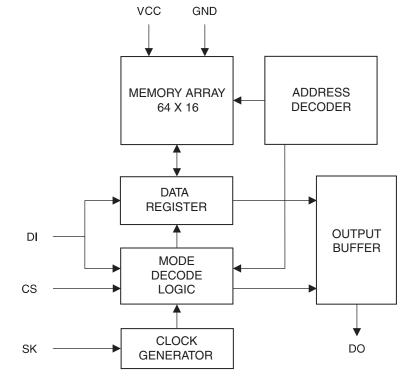


Table 2. Pin Capacitance⁽¹⁾

Applicable over recommended operating range from $T_A = 25^{\circ}C$, f = 1.0 MHz, $V_{CC} = +5.0V$ (unless otherwise noted)

Symbol	Test Conditions	Мах	Units	Conditions
C _{OUT}	Output Capacitance (DO)	5	pF	$V_{OUT} = 0V$
C _{IN}	Input Capacitance (CS, SK, DI)	5	pF	$V_{IN} = 0V$

Note: This parameter is characterized and is not 100% tested.

Table 3. DC Characteristics

Applicable over recommended operating range from: $T_{AI} = -40^{\circ}C$ to $+85^{\circ}C$, $V_{CC} = +1.8V$ to +5.5V, (unless otherwise noted)

Symbol	Parameter	Test Condition		Min	Тур	Мах	Units
V _{CC1}	Supply Voltage			1.8		5.5	V
V _{CC2}	Supply Voltage			2.7		5.5	V
V _{CC3}	Supply Voltage			4.5		5.5	V
1	Oursely Oursent	<u> хи с оу</u>	Read at 1.0 MHz		0.5	2.0	mA
I _{CC}	Supply Current	$V_{CC} = 5.0V$	Write at 1.0 MHz		0.5	2.0	mA
I _{SB1}	Standby Current	$V_{\rm CC} = 1.8V$	CS = 0V		14.0	20.0	μA
I _{SB2}	Standby Current	$V_{CC} = 2.7 V$	CS = 0V		14.0	20.0	μA
I _{SB3}	Standby Current	$V_{CC} = 5.0V$	CS = 0V		35.0	50.0	μA
I	Input Leakage	$V_{IN} = 0V$ to V_{CC}			0.1	1.0	μA
I _{OL}	Output Leakage	$V_{IN} = 0V$ to V_{CC}	$V_{IN} = 0V$ to V_{CC}		0.1	1.0	μA
V _{IL1} ⁽¹⁾ V _{IH1} ⁽¹⁾	Input Low Voltage Input High Voltage	$2.7V \le V_{CC} \le 5.5V$		-0.6 2.0		0.8 V _{CC} + 1	V
$V_{IL2}^{(1)}$ $V_{IH2}^{(1)}$	Input Low Voltage Input High Voltage	$1.8V \le V_{CC} \le 2.7V$		-0.6 V _{CC} x 0.7		V _{CC} x 0.3 V _{CC} + 1	V
V _{OL1}	Output Low Voltage		I _{OL} = 2.1 mA			0.4	V
V _{OH1}	Output High Voltage	$2.7V \le V_{CC} \le 5.5V$	I _{OH} = -0.4 mA	2.4			V
V _{OL2}	Output Low Voltage		I _{OL} = 0.15 mA			0.2	V
V _{OH2}	Output High Voltage	$1.8V \le V_{CC} \le 2.7V$	I _{OH} = -100 μA	V _{CC} -0.2			V

Note: 1. V_{IL} min and V_{IH} max are reference only and are not tested.





Table 4. AC Characteristics

Applicable over recommended operating range from $T_A = -40^{\circ}C$ to + 85°C, $V_{CC} = +2.5V$ to + 5.5V, CL = 1 TTL Gate and 100 pF (unless otherwise noted)

Symbol	Parameter	Test Condition		Min	Тур	Max	Units
f _{sк}	SK Clock Frequency	$\begin{array}{l} 4.5V \leq V_{CC} \leq 5.5V \\ 2.7V \leq V_{CC} \leq 5.5V \\ 1.8V \leq V_{CC} \leq 5.5V \end{array}$	/	0 0 0		2 1 0.25	MHz
t _{SKH}	SK High Time	$\begin{array}{l} 4.5V \leq V_{CC} \leq 5.5 \\ 2.7V \leq V_{CC} \leq 5.5 \\ 1.8V \leq V_{CC} \leq 5.5 \\ \end{array}$	/	250 250 1000			ns
t _{SKL}	SK Low Time	$\begin{array}{l} 4.5V \leq V_{CC} \leq 5.5 \\ 2.7V \leq V_{CC} \leq 5.5 \\ 1.8V \leq V_{CC} \leq 5.5 \\ \end{array}$	/	250 250 1000			ns
t _{cs}	Minimum CS Low Time	$\begin{array}{l} 4.5V \leq V_{CC} \leq 5.5 \\ 2.7V \leq V_{CC} \leq 5.5 \\ 1.8V \leq V_{CC} \leq 5.5 \end{array}$	/	250 250 1000			ns
t _{CSS}	CS Setup Time	Relative to SK	$\begin{array}{l} 4.5V \leq V_{CC} \leq 5.5V \\ 2.7V \leq V_{CC} \leq 5.5V \\ 1.8V \leq V_{CC} \leq 5.5V \end{array}$	50 50 200			ns
t _{DIS}	DI Setup Time	Relative to SK	$\begin{array}{l} 4.5V \leq V_{CC} \leq 5.5V \\ 2.7V \leq V_{CC} \leq 5.5V \\ 1.8V \leq V_{CC} \leq 5.5V \end{array}$	100 100 400			ns
t _{CSH}	CS Hold Time	Relative to SK		0			ns
t _{DIH}	DI Hold Time	Relative to SK	$\begin{array}{l} 4.5V \leq V_{CC} \ \leq 5.5V \\ 2.7V \leq V_{CC} \ \leq 5.5V \\ 1.8V \leq V_{CC} \ \leq 5.5V \end{array}$	100 100 400			ns
t _{PD1}	Output Delay to "1"	AC Test	$\begin{array}{l} 4.5V \leq V_{CC} \; \leq 5.5V \\ 2.7V \leq V_{CC} \; \leq 5.5V \\ 1.8V \leq V_{CC} \; \leq 5.5V \end{array}$			250 250 1000	ns
t _{PD0}	Output Delay to "0"	AC Test	$ \begin{array}{l} 4.5V \leq V_{CC} \leq 5.5V \\ 2.7V \leq V_{CC} \leq 5.5V \\ 1.8V \leq V_{CC} \leq 5.5V \end{array} \\ \end{array} $			250 250 1000	ns
t _{SV}	CS to Status Valid	AC Test	$ \begin{array}{c} 4.5V \leq V_{CC} \leq 5.5V \\ 2.7V \leq V_{CC} \leq 5.5V \\ 1.8V \leq V_{CC} \leq 5.5V \end{array} \\ \end{array} $			250 250 1000	ns
t _{DF}	CS to DO in High Impedance	AC Test CS = V _{IL}	$\begin{array}{c} 4.5V \leq V_{CC} \leq 5.5V \\ 2.7V \leq V_{CC} \leq 5.5V \\ 1.8V \leq V_{CC} \leq 5.5V \end{array}$			100 100 400	ns
t _{WP}	Write Cycle Time			0.1	3	10	ms
Endurance ⁽¹⁾	5.0V, 25°C			1M			Write Cycle

Note: 1. This parameter is characterized and is not 100% tested.

4

Functional Description

The AT93C46A is accessed via a simple and versatile three-wire serial communication interface. Device operation is controlled by seven instructions issued by the host processor. *A valid instruction starts with a rising edge of CS* and consists of a start bit (logic "1") followed by the appropriate op code and the desired memory address location.

			Address	
Instruction	SB	Op Code	x 16	Comments
READ	1	10	$A_5 - A_0$	Reads data stored in memory, at specified address
EWEN	1	00	11XXXX	Write enable must precede all programming modes
ERASE	1	11	$A_{5} - A_{0}$	Erase memory location $A_n - A_0$
WRITE	1	01	$A_5 - A_0$	Writes memory location $A_n - A_0$
ERAL	1	00	10XXXX	Erases all memory locations. Valid only at $V_{CC} = 4.5V$ to 5.5V
WRAL	1	00	01XXXX	Writes all memory locations. Valid only at $V_{CC} = 4.5V$ to 5.5V
EWDS	1	00	00XXXX	Disables all programming instructions

Table 5.	Instruction	Set for the	AT93C46A
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READ (READ): The Read (READ) instruction contains the address code for the memory location to be read. After the instruction and address are decoded, data from the selected memory location is available at the serial output pin DO. Output data changes are synchronized with the rising edges of serial clock SK. It should be noted that a dummy bit (logic "0") precedes the 16-bit data output string.

ERASE/WRITE ENABLE (EWEN): To assure data integrity, the part automatically goes into the Erase/Write Disable (EWDS) state when power is first applied. An Erase/Write Enable (EWEN) instruction must be executed first before any programming instructions can be carried out. Please note that once in the EWEN state, programming remains enabled until an EWDS instruction is executed or V_{CC} power is removed from the part.

ERASE (ERASE): The Erase (ERASE) instruction programs all bits in the specified memory location to the logical "1" state. The self-timed erase cycle starts once the Erase instruction and address are decoded. The DO pin outputs the ready/busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). A logic "1" at pin DO indicates that the selected memory location has been erased and the part is ready for another instruction.

WRITE (WRITE): The Write (WRITE) instruction contains the 16 bits of data to be written into the specified memory location. The self-timed programming cycle, t_{WP} , starts after the last bit of data is received at serial data input pin DI. The DO pin outputs the ready/busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). A logic "0" at DO indicates that programming is still in progress. A logic "1" indicates that the memory location at the specified address has been written with the data pattern contained in the instruction and the part is ready for further instructions. *A ready/busy status cannot be obtained if the CS is brought high after the end of the self-timed programming cycle, t_{WP}*

ERASE ALL (ERAL): The Erase All (ERAL) instruction programs every bit in the memory array to the logic "1" state and is primarily used for testing purposes. The DO pin outputs the ready/busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). The ERAL instruction is valid only at V_{CC} = $5.0V \pm 10\%$.

WRITE ALL (WRAL): The Write All (WRAL) instruction programs all memory locations with the data patterns specified in the instruction. The DO pin outputs the ready/busy





status of the part if CS is brought high after being kept low for a minimum of 250 ns (t_{CS}). The WRAL instruction is valid only at V_{CC} = $5.0V \pm 10\%$.

ERASE/WRITE DISABLE (EWDS): To protect against accidental data disturb, the Erase/Write Disable (EWDS) instruction disables all programming modes and should be executed after all programming operations. The operation of the Read instruction is independent of both the EWEN and EWDS instructions and can be executed at any time.

Timing Diagrams

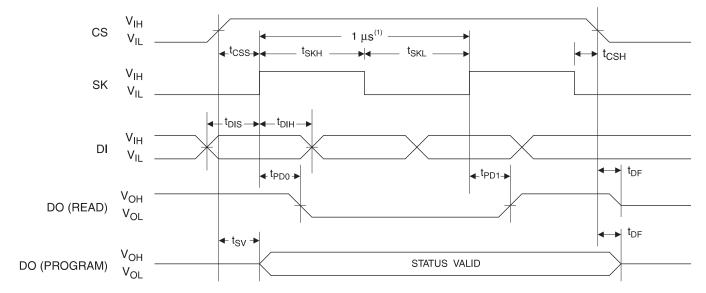


Figure 2. Synchronous Data Timing

Note: 1. This is the minimum SK period.

Table el elgamzadon neg lei in		
	AT93C46A	
I/O	x 16	
A _N	A ₅	
D _N	D ₁₅	

Table 6. Organization Key for Timing Diagrams

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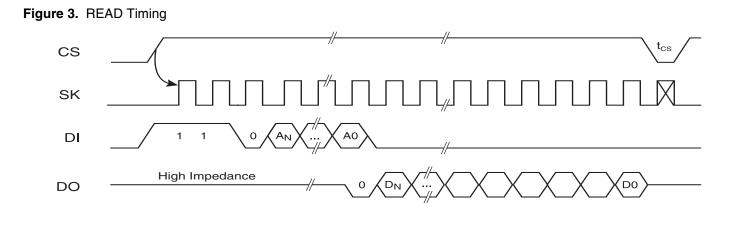
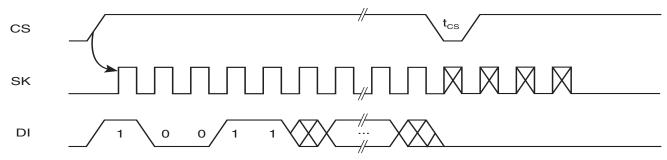
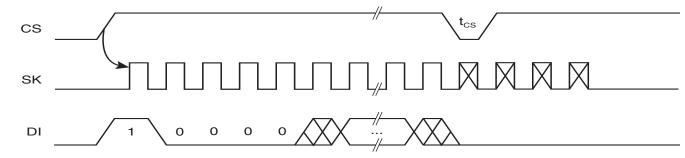


Figure 4. EWEN Timing¹



Note: 1. Requires a minimum of nine clock cycles.





Note: 1. Requires a minimum of nine clock cycles.





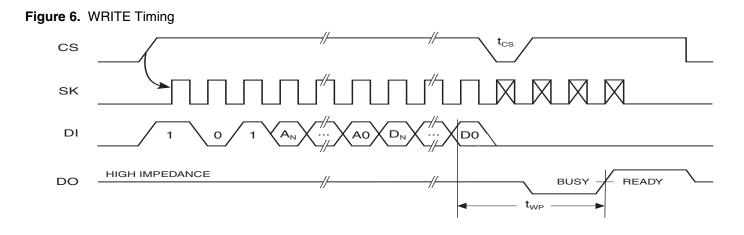
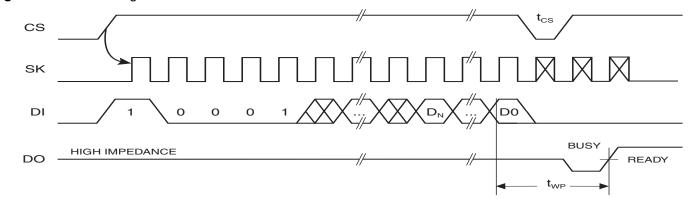


Figure 7. WRAL Timing^{(1),(2)}



Notes: 1. Valid only at V_{CC} = 4.5V to 5.5V. 2. Requires a minimum of nine clock cycles.

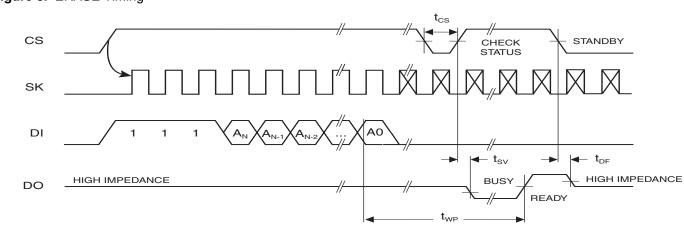
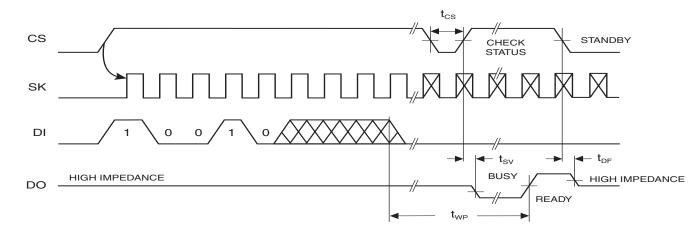


Figure 8. ERASE Timing

AT93C46A

Figure 9. ERAL Timing⁽¹⁾



Note: 1. Valid only at $V_{CC} = 4.5V$ to 5.5V.





Ordering Information

Ordering Code	Package	Operation Range	
AT93C46A-10PI-2.7	8P3	Induction	
AT93C46A-10SI-2.7	8S1	Industrial	
AT93C46A-10TI-2.7	8A2	(–40°C to 85°C)	
AT93C46A-10PI-1.8	8P3	Industrial	
AT93C46A-10SI-1.8	8S1		
AT93C46A-10TI-1.8	8A2	(−40°C to 85°C)	
AT93C46A-10PU-2.7	8P3		
AT93C46A-10PU-1.8	8P3		
AT93C46A-10SU-2.7	8S1	Lead-free/Halogen-free/ Industrial Temperature	
AT93C46A-10SU-1.8	8S1	(-40°C to 85°C)	
AT93C46A-10TU-2.7	8A2	(-40 0 10 85 0)	
AT93C46A-10TU-1.8	8A2		

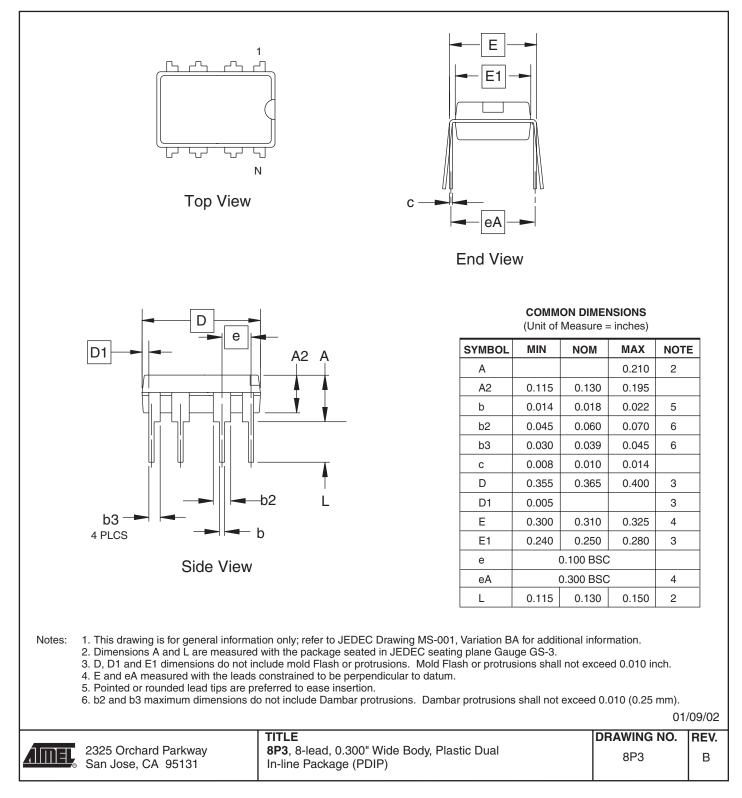
Note: For 2.7V devices used in the 4.5V to 5.5V range, please refer to performance values in Table 3 on page 3 and Table 4 on page 4.

Package Type			
8P3	8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)		
8S1	8S1 8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)		
8A2	A2 8-lead, 0.170" Wide, Thin Small Outline Package (TSSOP)		
	Options		
-2.7	Low Voltage (2.7V to 5.5V)		
-1.8	Low Voltage (1.8V to 5.5V)		

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Packaging Information

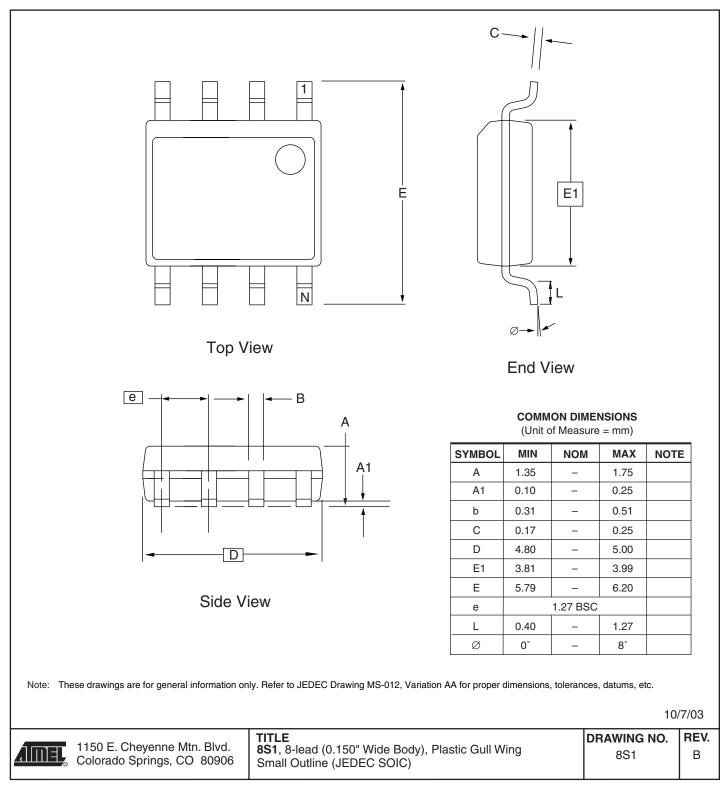
8P3 – PDIP



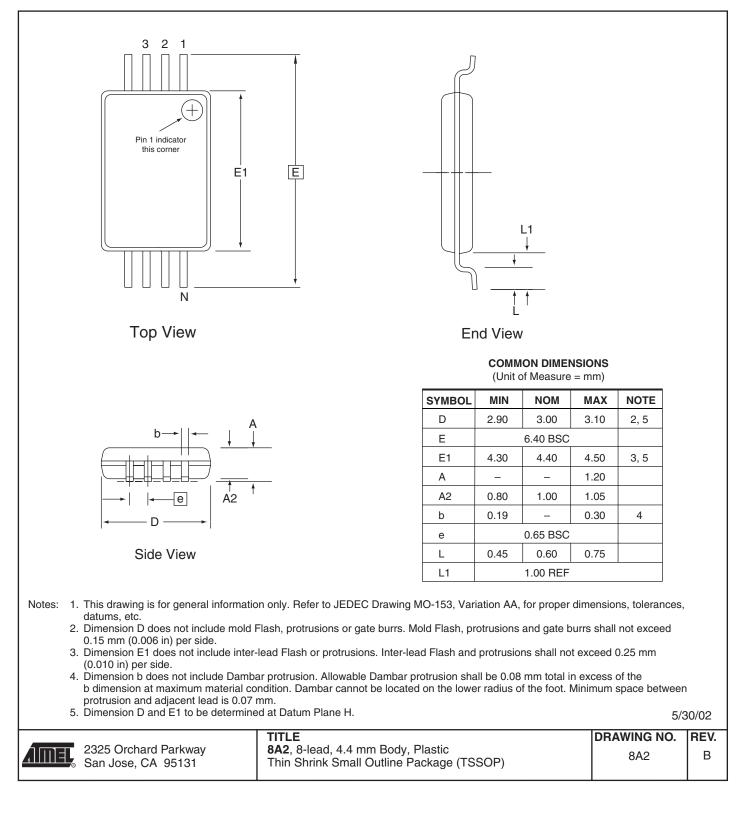




8S1 – JEDEC SOIC



8A2 – TSSOP







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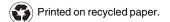
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